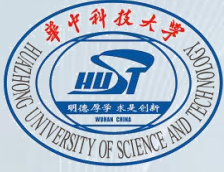


Huazhong University
of Science & Technology

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School of Electronic Information
and Communications

Jiaqing Huang



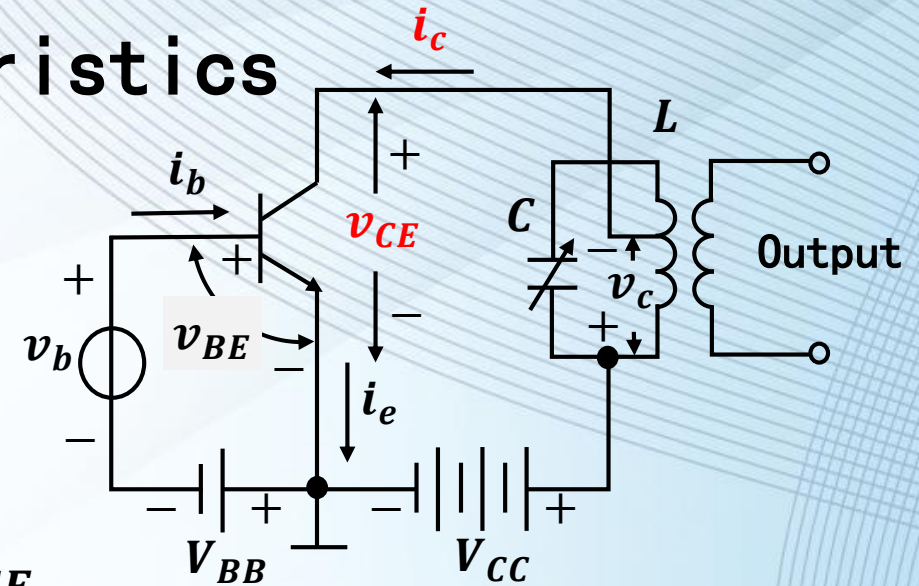
Dynamic Characteristics

RF Power Amplifier-Dynamic Characteristics

➤ Static Characteristics: No Load

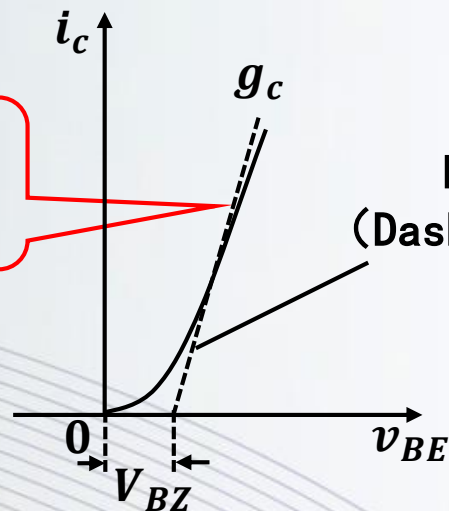
If has load, $i_c \uparrow$, R_L has voltage, v_{CE} changes

➤ Dynamic Characteristics: Curve between i_c & v_{CE}

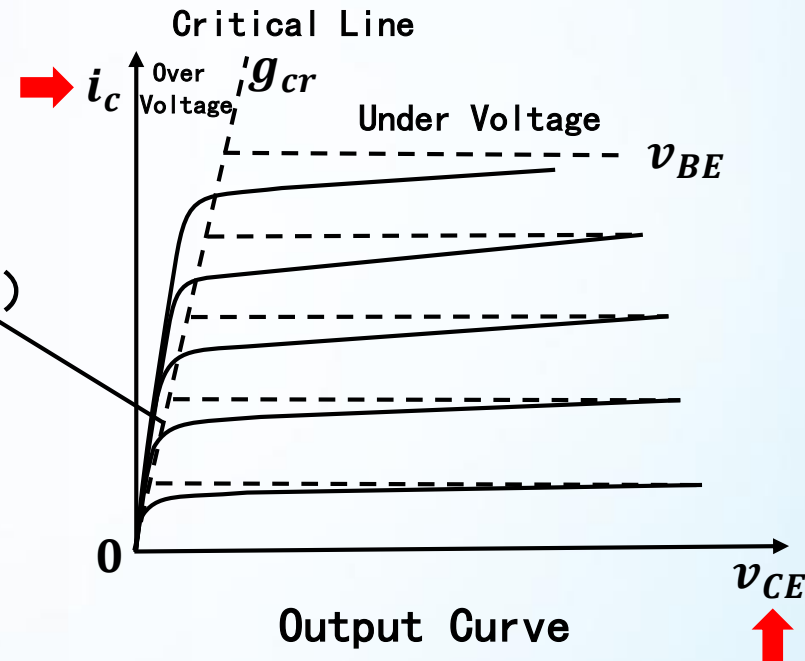


$$i_c = g_c(v_{BE} - V_{BZ})$$

Transfer Equation



Transfer Curve



Output Curve

RF Power Amplifier-Dynamic Characteristics

➤ When resonant, we have 2 circuit equations:

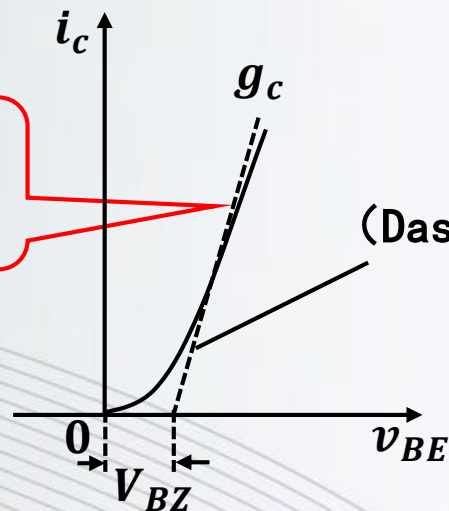
$$\begin{cases} v_{BE} = -V_{BB} + V_{bm} \cos \omega t \\ v_{CE} = V_{CC} - V_{cm} \cos \omega t \end{cases}$$

Cancel $\cos \omega t$, Obtain

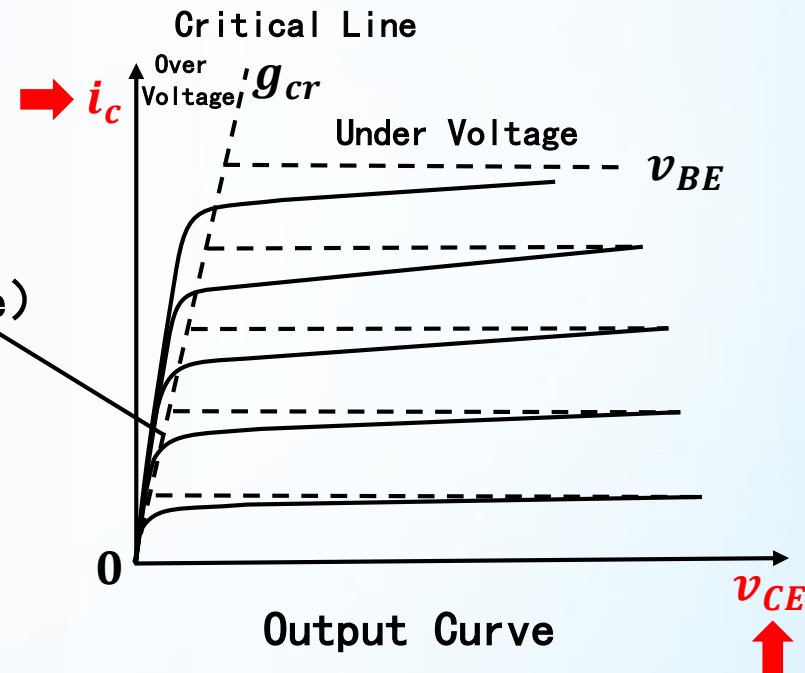
$$v_{BE} = -V_{BB} + V_{bm} \frac{V_{CC} - v_{CE}}{V_{cm}}$$

$$i_c = g_c(v_{BE} - V_{BZ})$$

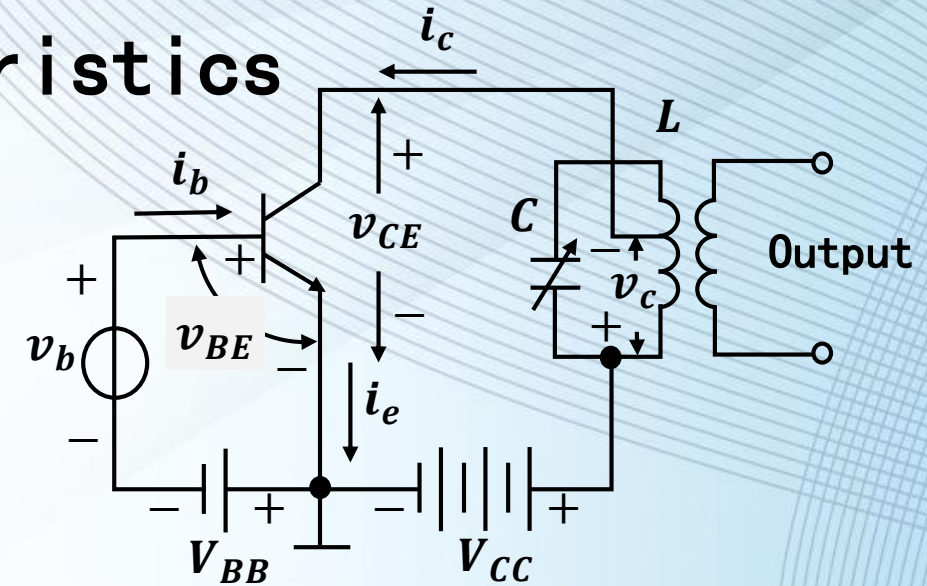
Transfer Equation



Transfer Curve



Output Curve



RF Power Amplifier-Dynamic Characteristics

$$i_c = g_c(v_{BE} - V_{BZ}) \text{ Transfer Equation}$$

$$v_{BE} = -V_{BB} + V_{bm} \frac{V_{CC} - v_{CE}}{V_{cm}}$$

Obtain Dynamic Curve on i_c - v_{CE} Plane:

$$i_c = g_c \left[-V_{BB} + V_{bm} \frac{(V_{CC} - v_{CE})}{V_{cm}} - V_{BZ} \right]$$

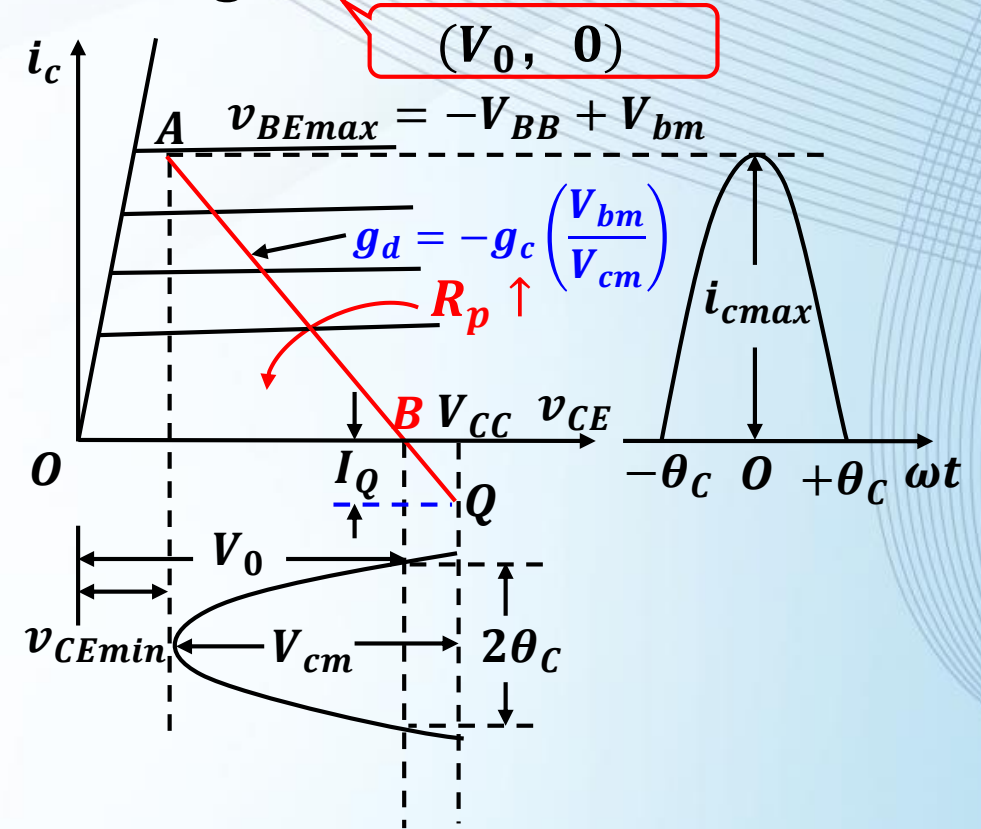
$$= -g_c \left(\frac{V_{bm}}{V_{cm}} \right) \left[v_{CE} - \frac{V_{CC}V_{bm} - V_{BZ}V_{cm} - V_{BB}V_{cm}}{V_{bm}} \right]$$

$$= g_d(v_{CE} - V_0)$$

$$\text{Slope: } g_d = -g_c \left(\frac{V_{bm}}{V_{cm}} \right) = -g_c \frac{V_{bm}}{I_{cm1} R_p}$$

Intercept: V_0

➤ Method 1: Line with slope g_d , goes through B Point



i_c - v_{CE} Dynamic Curve

➤ **Negative Slope:** Negative Resistance, AC Energy Generator

RF Power Amplifier-Dynamic Characteristics

➤ Method 2: Line pass points A & Q

$$\begin{cases} v_{BE} = -V_{BB} + V_{bm} \cos \omega t \\ v_{CE} = V_{CC} - V_{cm} \cos \omega t \end{cases}$$

$$(v_{CEmin}, i_{cmax})$$

① A : $\omega t = 0$, $i_c = i_{cmax}$

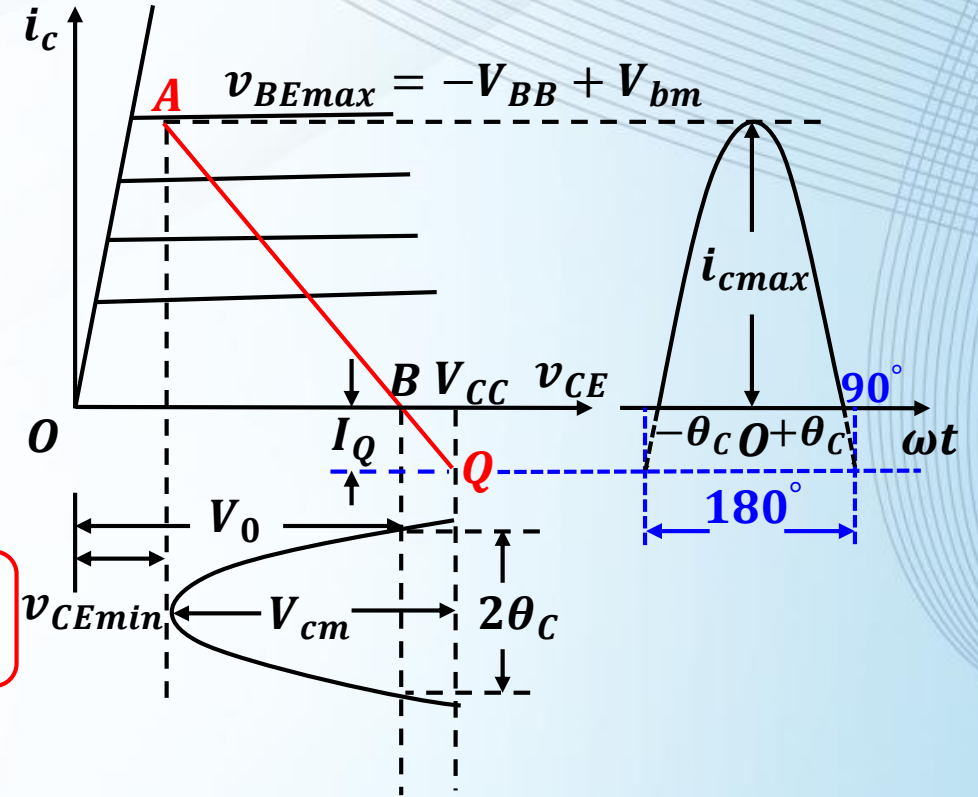
$$\begin{cases} v_{BE} = -V_{BB} + V_{bm} \Rightarrow i_{cmax} = g_c(-V_{BB} + V_{bm} - V_{BZ}) \\ v_{CE} = V_{CC} - V_{cm} = v_{CEmin} \end{cases}$$

$$(V_{CC}, I_Q)$$

② Q: $\omega t = 90^\circ$, $i_c = I_Q$

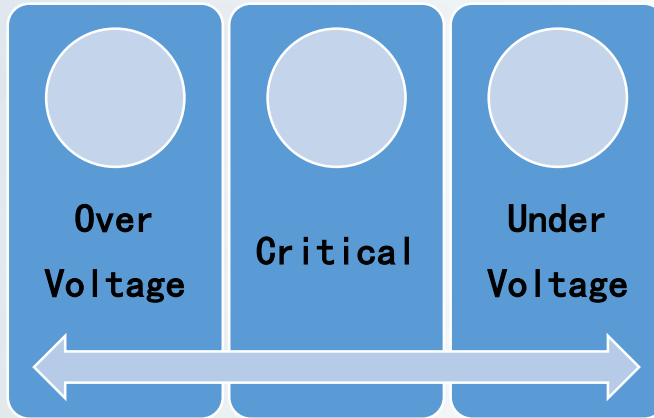
$$\begin{cases} v_{BE} = -V_{BB} \Rightarrow I_Q = g_c(-V_{BB} - V_{BZ}) \\ v_{CE} = V_{CC} \end{cases}$$

$$i_c = g_c(v_{BE} - V_{BZ})$$



$i_c - v_{CE}$ Dynamic Curve

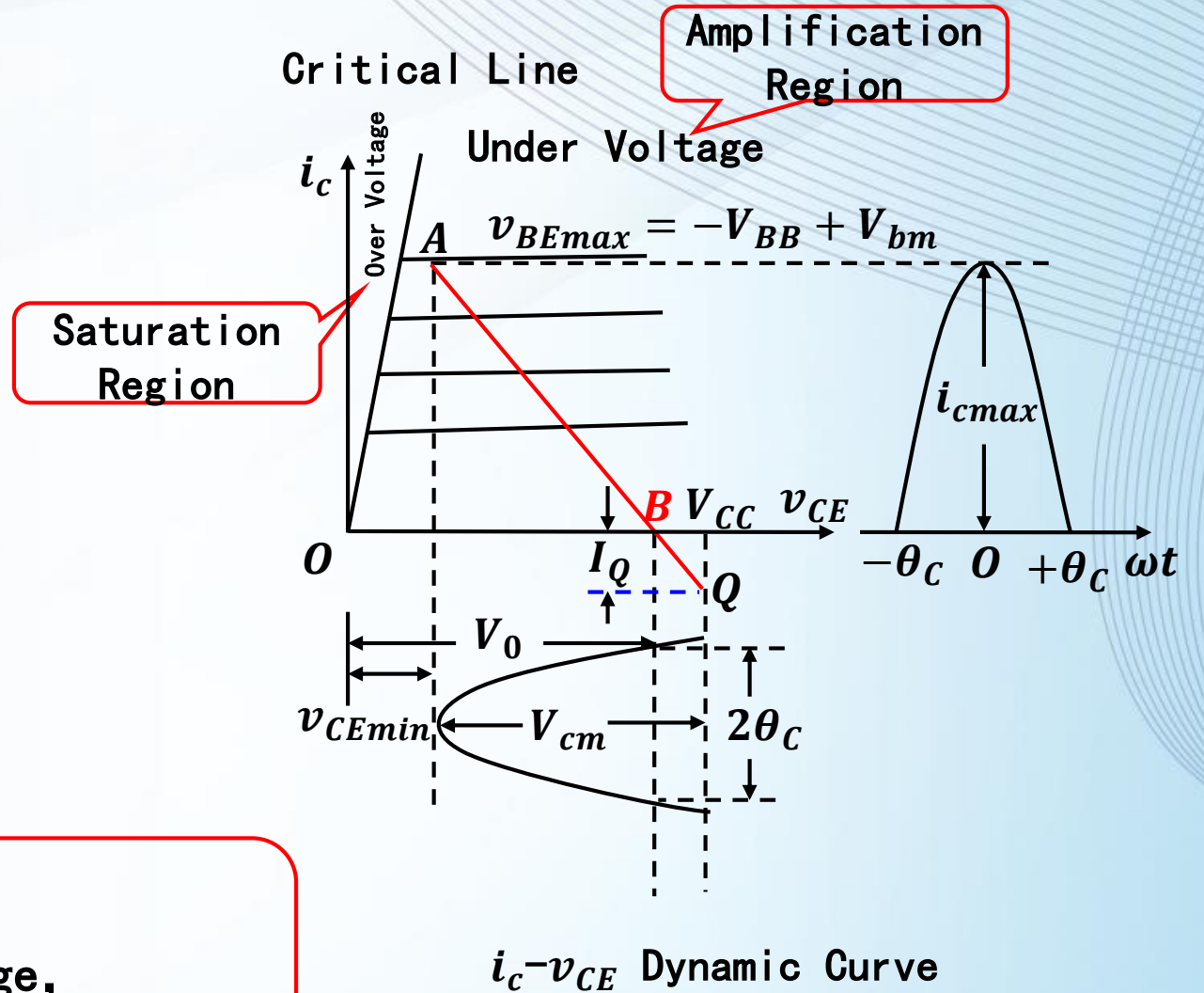
RF Power Amplifier-Dynamic Characteristics



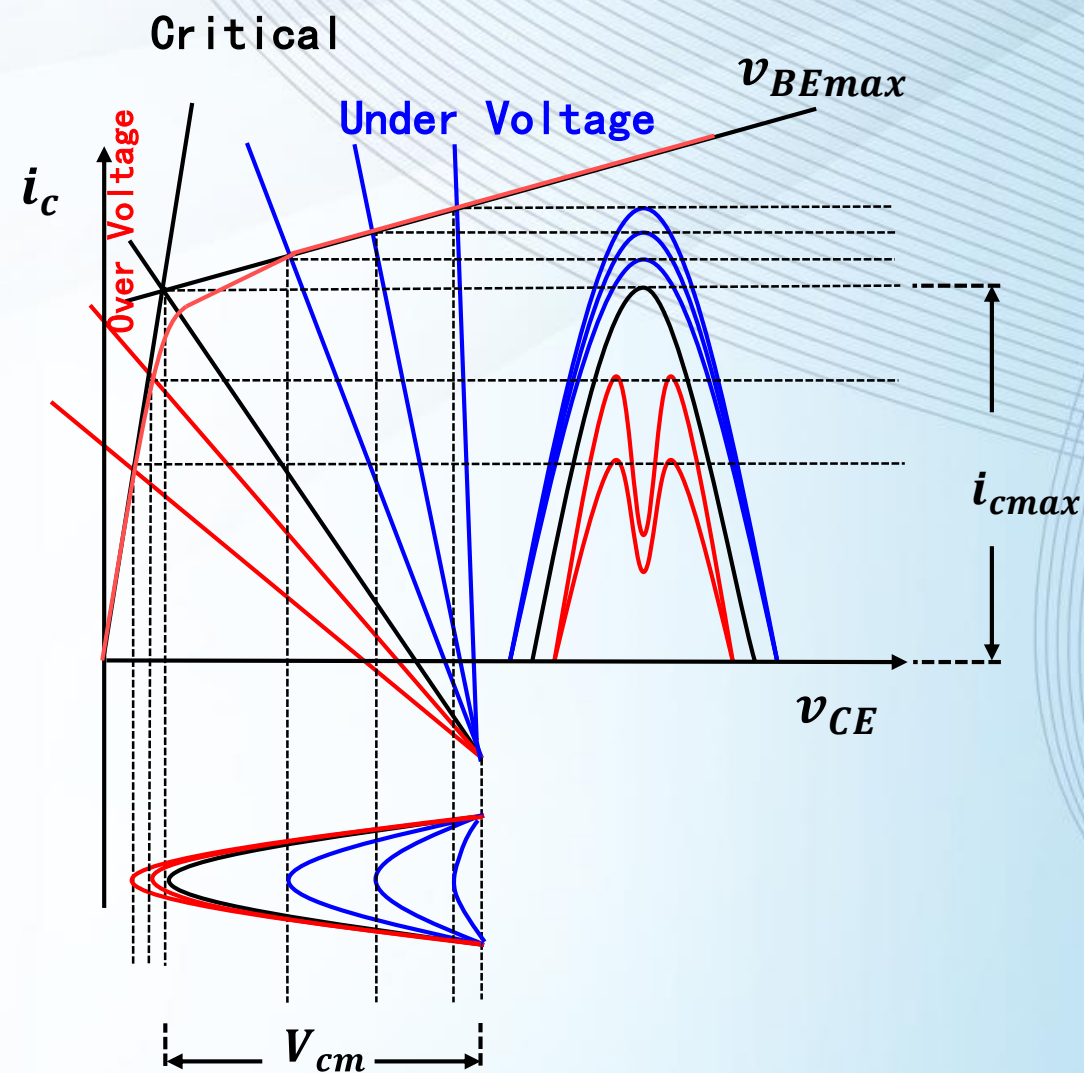
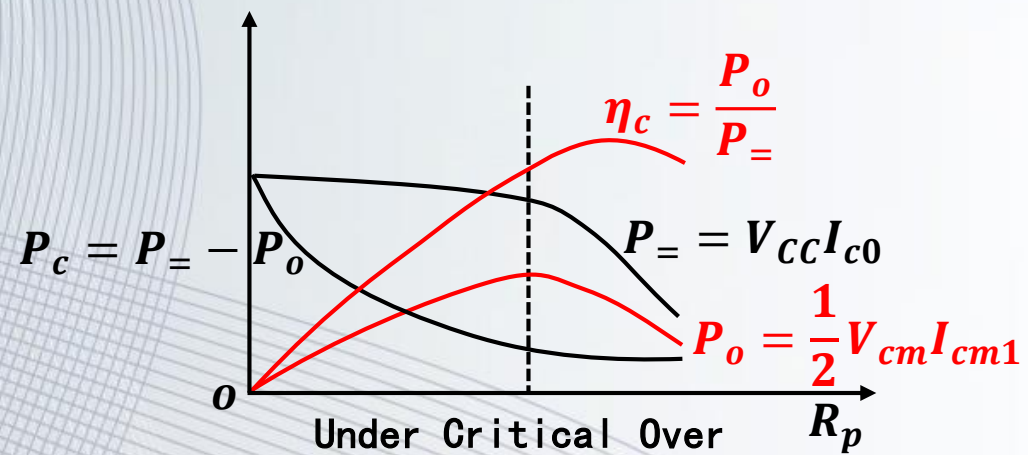
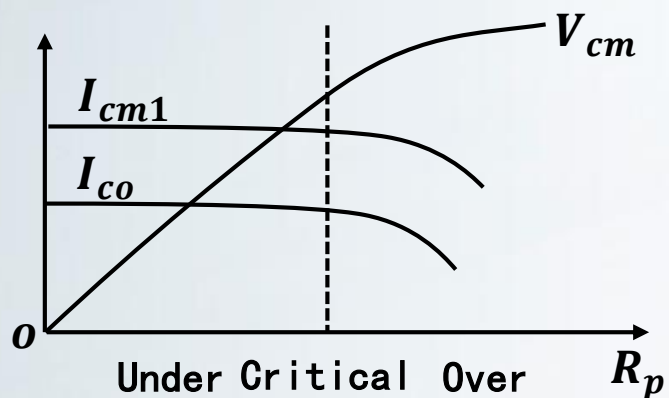
- Only change R_p
- Only change V_{CC}
- Only change V_{bm} (V_{BB})

Load Characteristics

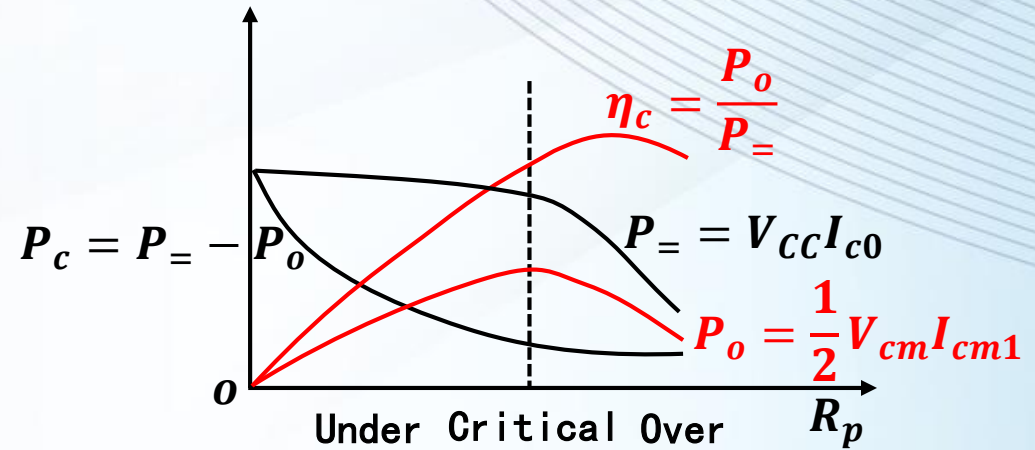
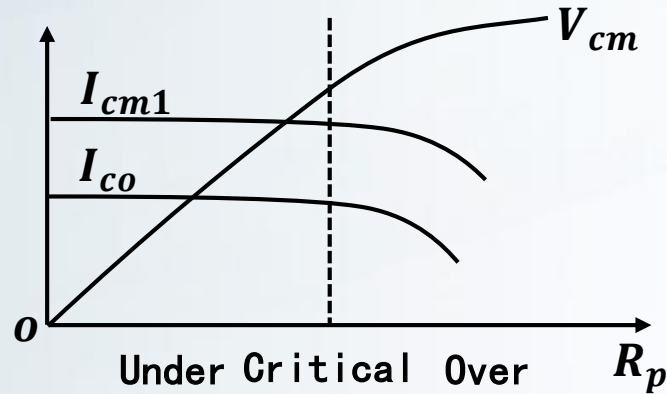
If V_{CC} 、 V_{bm} (V_{BB}) do not change,
Current/Voltage/ P_o / η_c will change with R_p



RF Power Amplifier- R_p



RF Power Amplifier- R_p



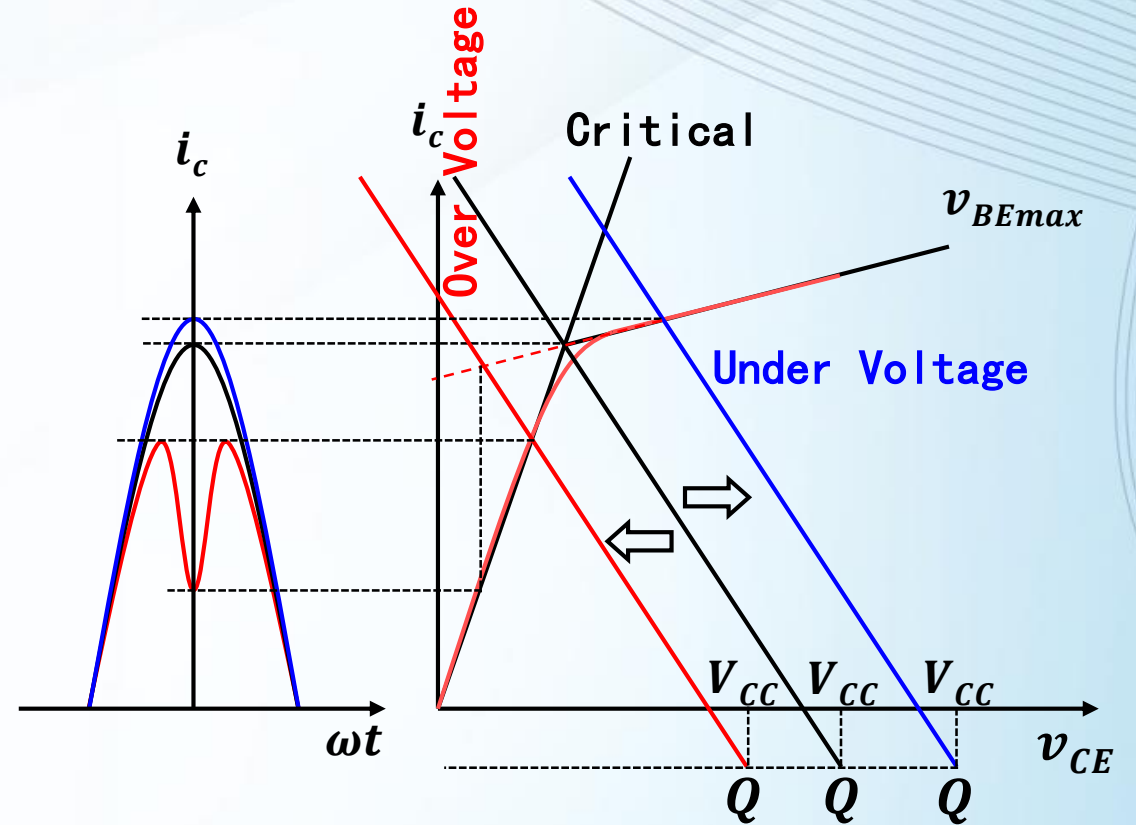
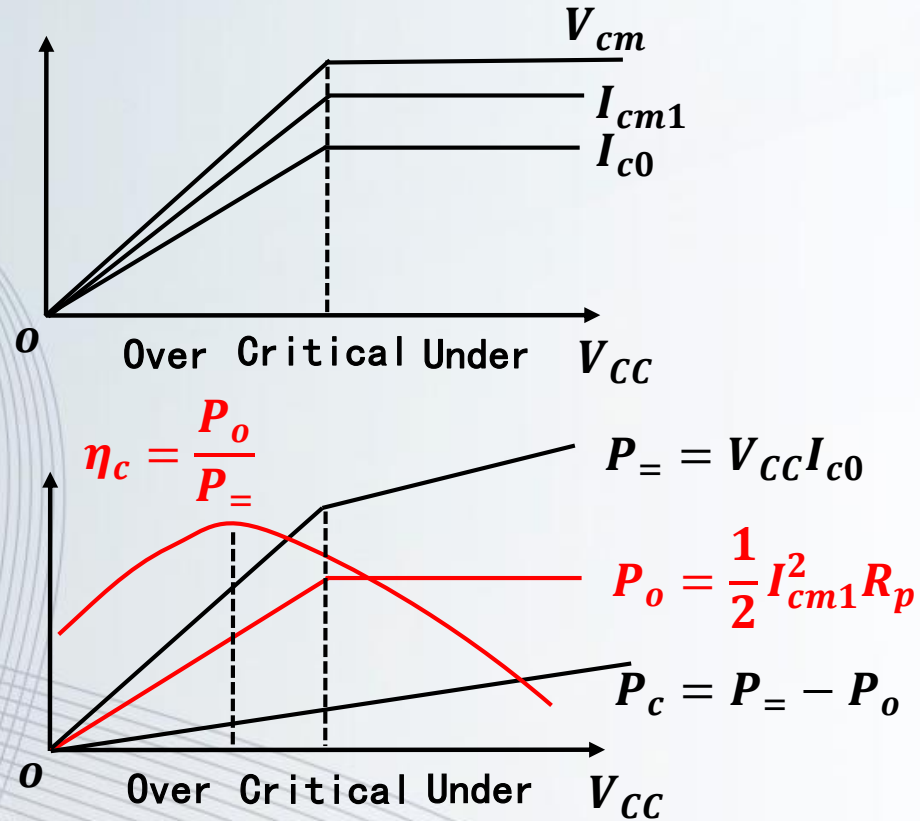
➤ Features of Working State:

- Under Voltage State: Constant Current, $P_o \downarrow$, $\eta_c \downarrow$, $P_c \uparrow$;
- Over Voltage State: Constant Voltage, $P_o \downarrow$, η_c max; **Middle Stage**
- Critical State: P_o max, η_c high; **Last Stage**

Best State

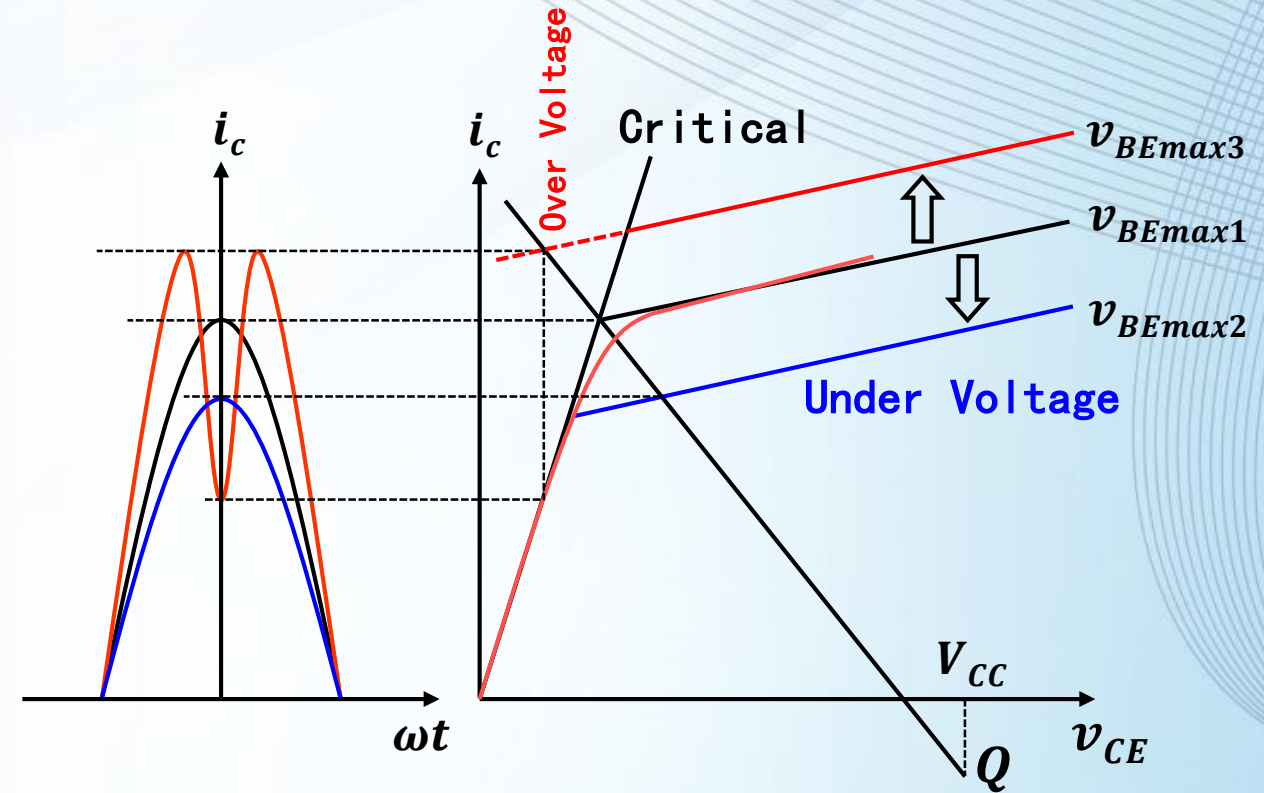
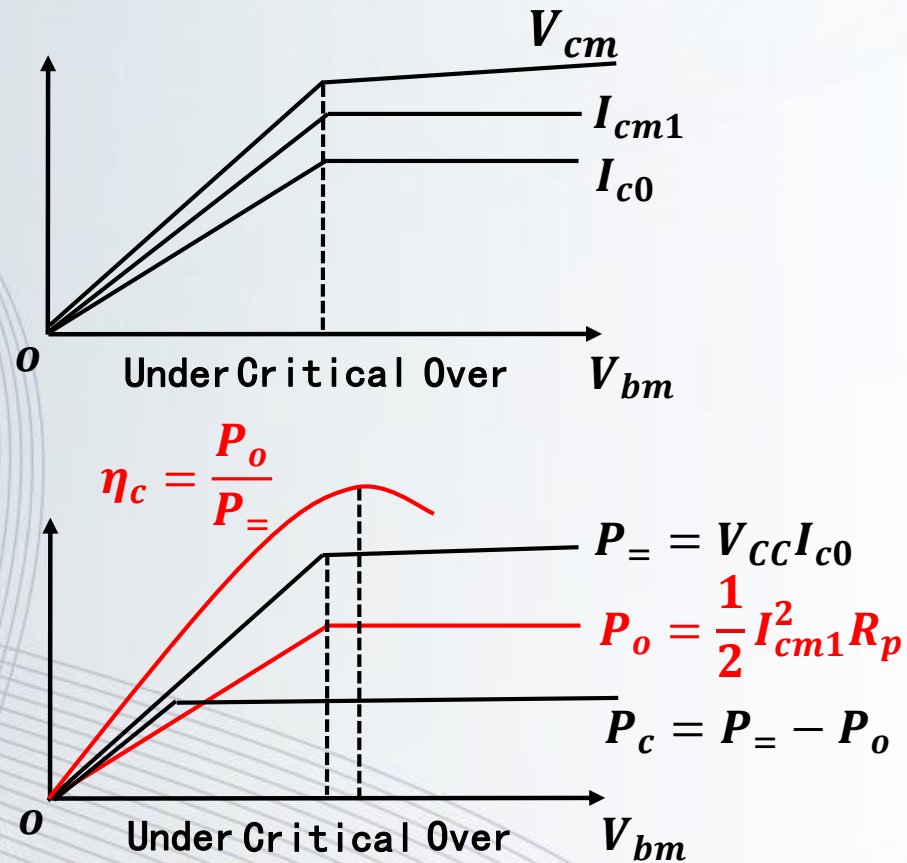
RF Power Amplifier (Dynamic Characteristics)— V_{CC}

➤ R_p 、 V_{bm} (V_{BB}) no change, V_{CC} vs. Over Voltage、Under Voltage

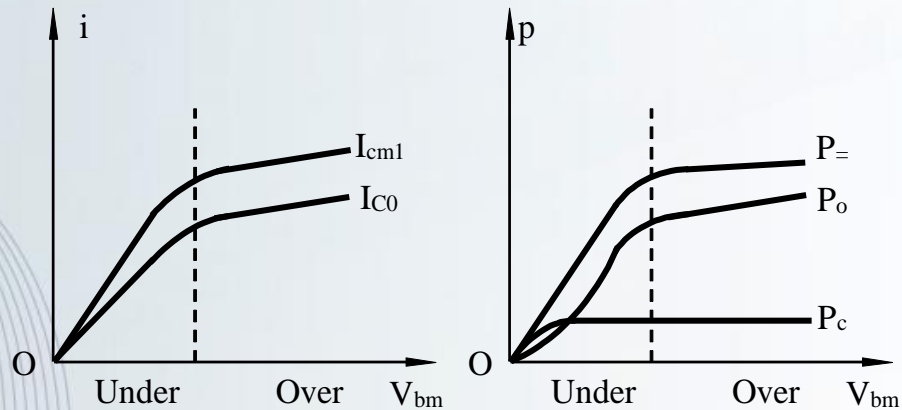


RF Power Amplifier (Dynamic Characteristics)— V_{bm}

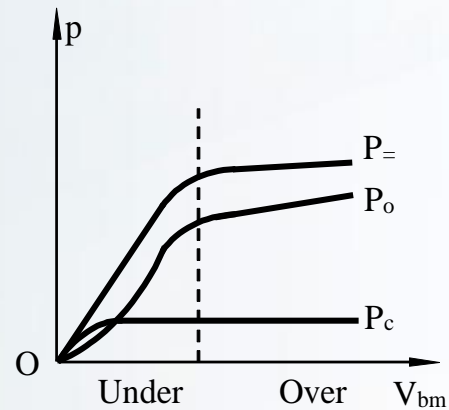
➤ R_p 、 V_{BB} 、 V_{CC} no change, V_{bm} vs. Over Voltage、Under Voltage



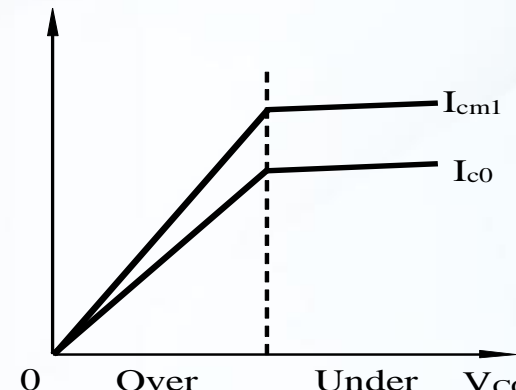
Ex 4-1 For a RF power amplifier, it is not effective to improve P_o by means of increasing V_{bm} . Analyze its reason and how to improve P_o effectively?



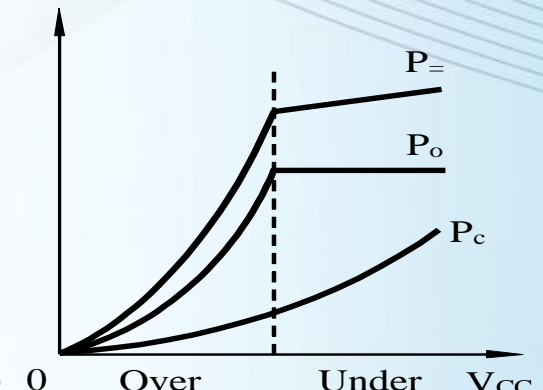
(a)



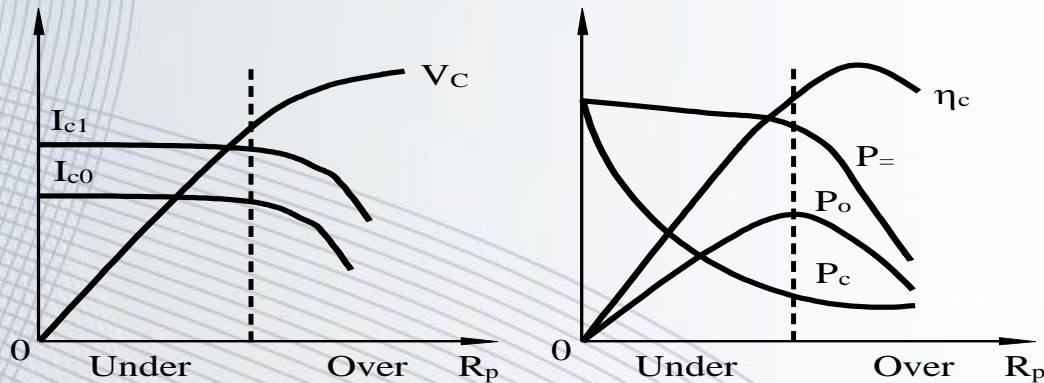
(b)



(a)



(b)



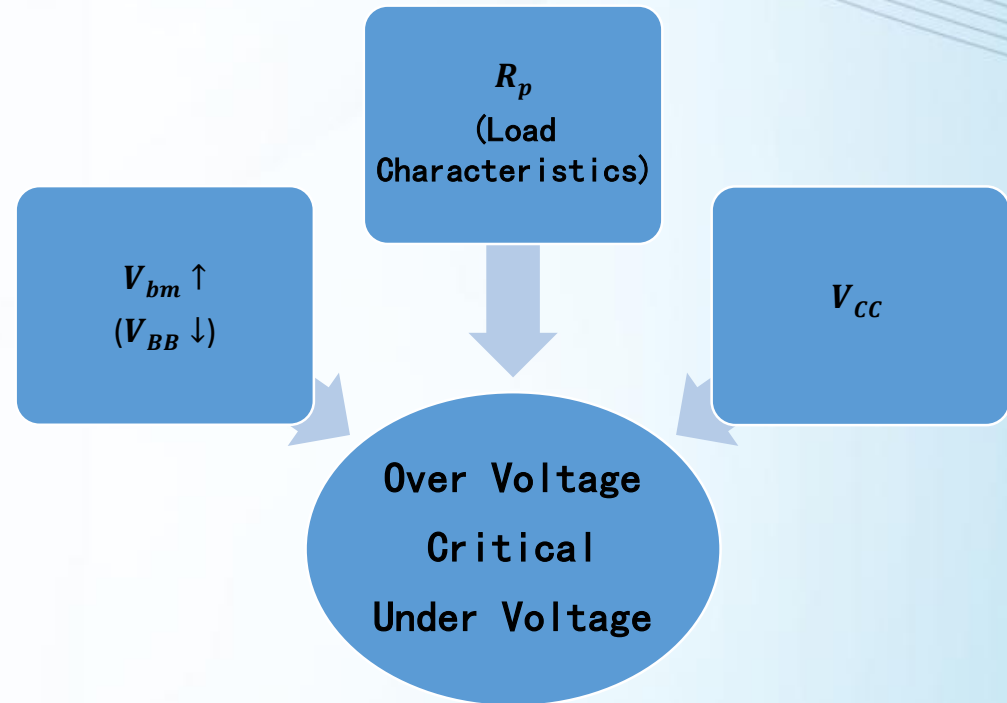
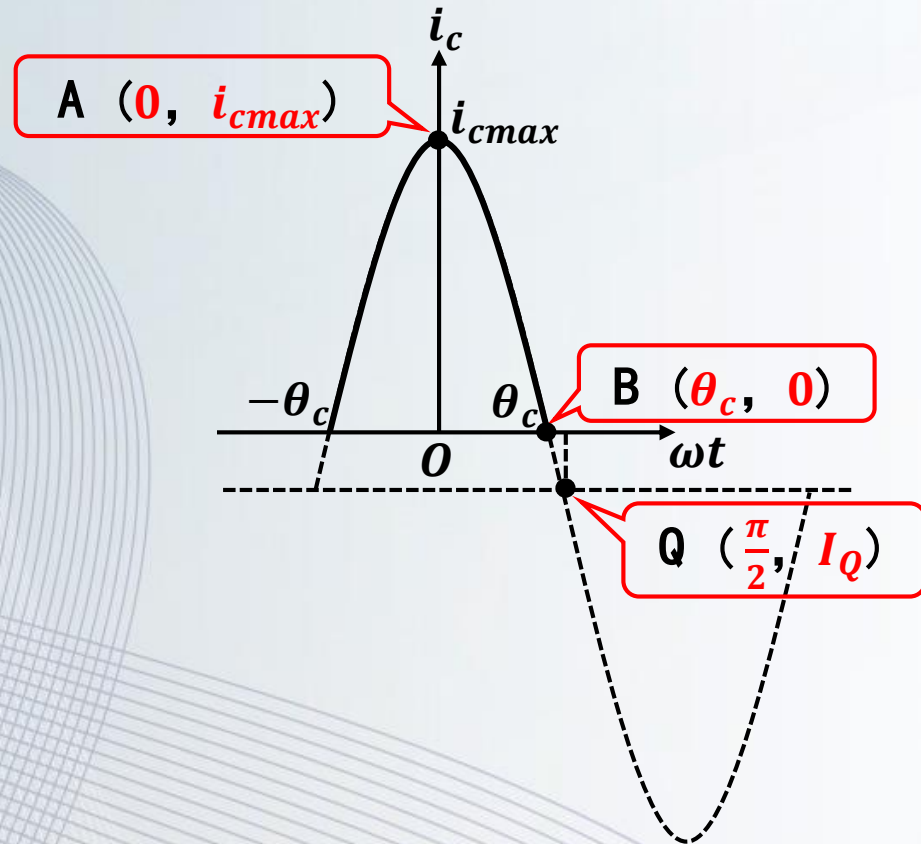
Load Curve

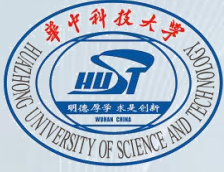
$V_{bm} \uparrow \rightarrow P_o \uparrow$ Ineffectively
 \Rightarrow **Over Voltage State**

$\Rightarrow P_o \uparrow$ by $\uparrow V_{cc}$ & $\downarrow R_p$

Summary

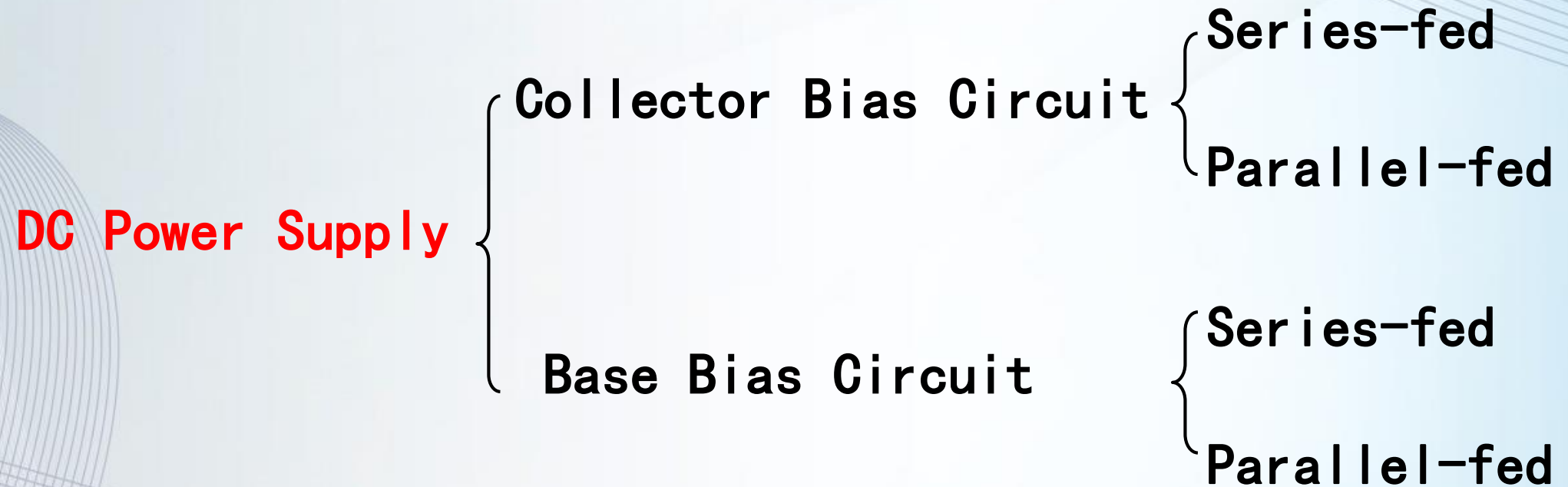
➤ Dynamic Characteristics (A B Q)





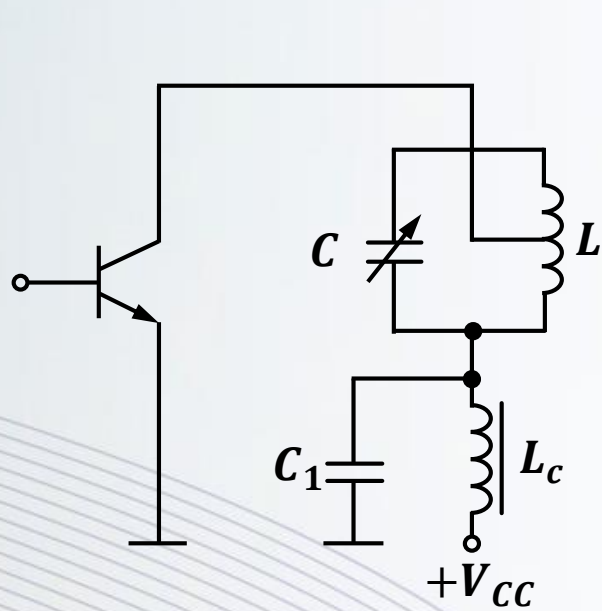
Power Amplifier Circuit

RF Power Amplifier—DC Power Supply Circuit

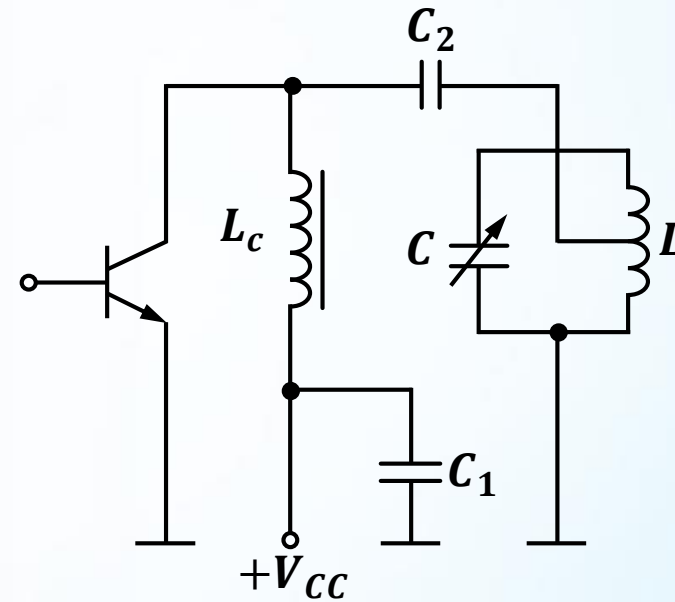


RF Power Amplifier—Collector Bias Circuit

➤ Include Series-fed & Parallel-fed



Series-fed

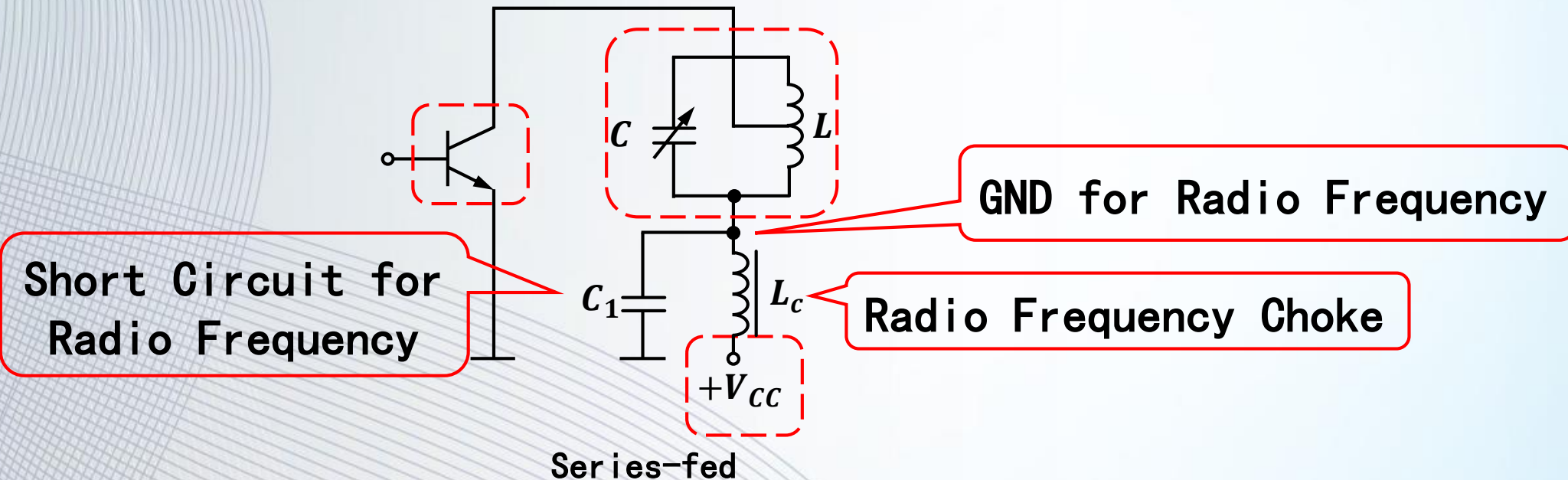


Parallel-fed

RF Power Amplifier—Collector Bias Circuit (Series-fed)

➤ Series-fed Circuit:

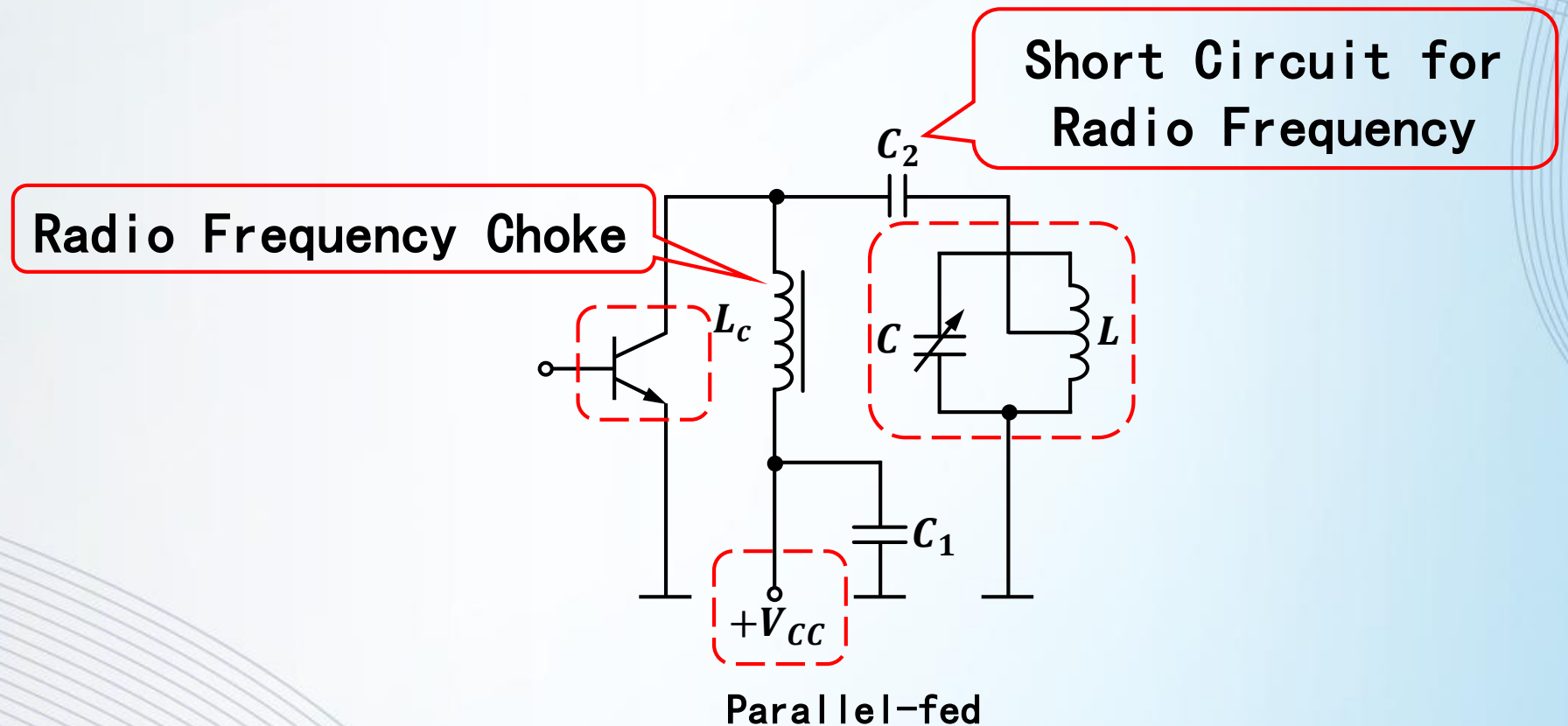
V_{CC} + Parallel Resonance + Power Amplifier Transistor



RF Power Amplifier—Collector Bias Circuit (Parallel-fed)

➤ Parallel-fed Circuit:

V_{CC} // Parallel Resonance // Power Amplifier Transistor

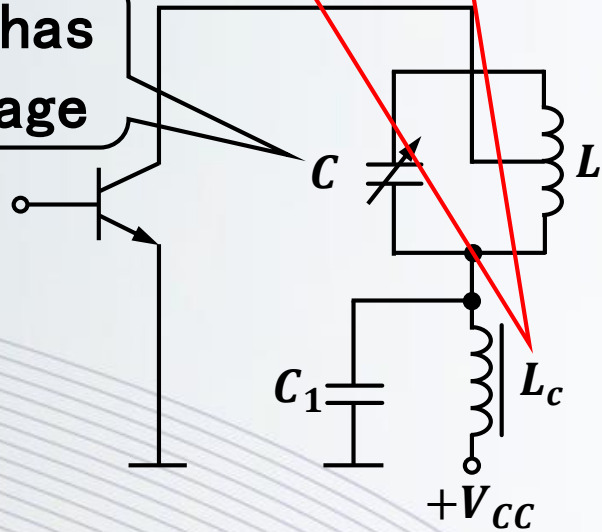


RF Power Amplifier—Collector Bias Circuit (Comparison)

➤ Series-fed *vs.* Parallel-fed

GND for Radio Frequency,
 L_c distributed capacitance ↓

Resonance C has
high DC voltage

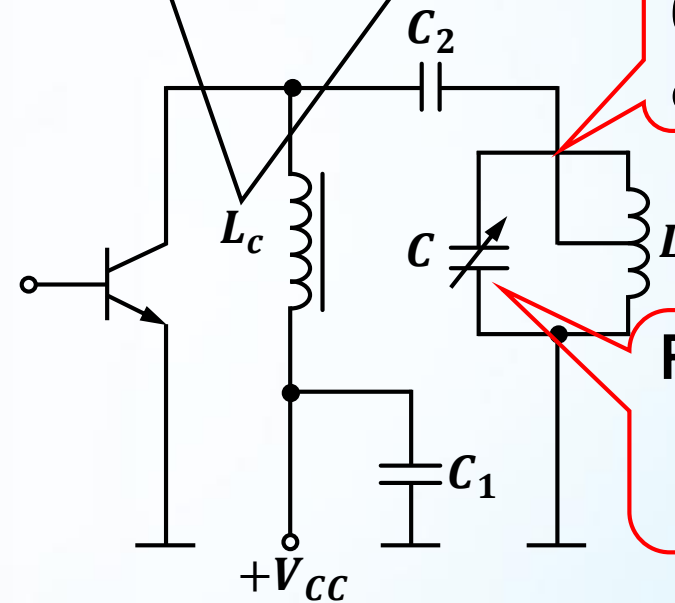


Series-fed

High Voltage for Radio Frequency,
 L_c distributed capacitance ↑

Instable

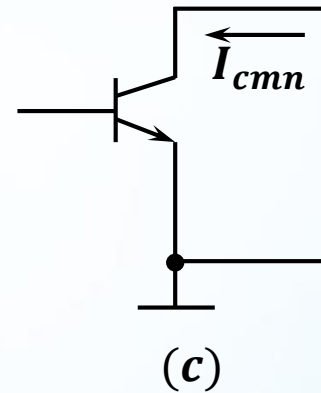
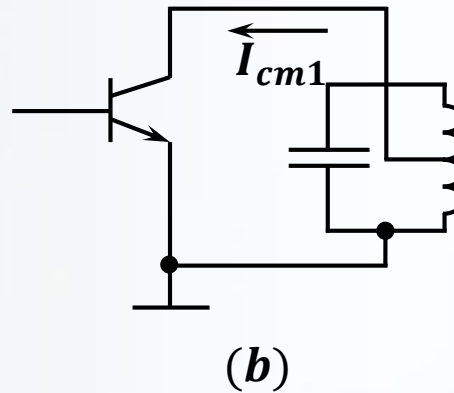
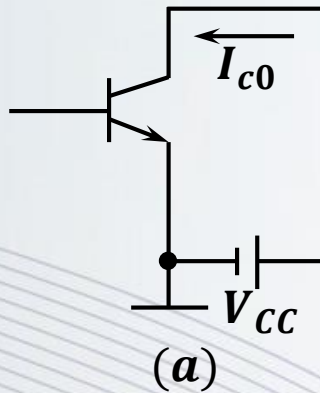
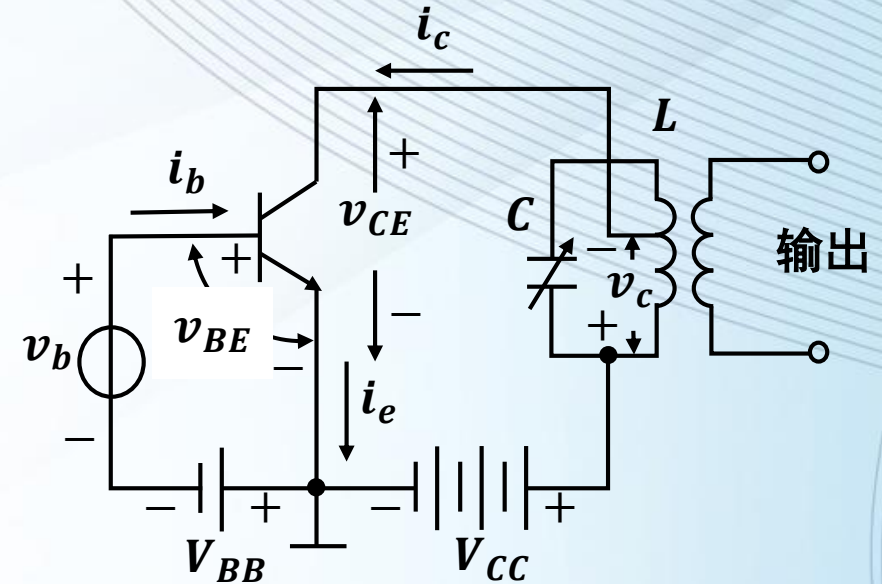
GND for both ends
of resonance



Parallel-fed

RF Power Amplifier—Collector Bias **Equivalent** Circuit

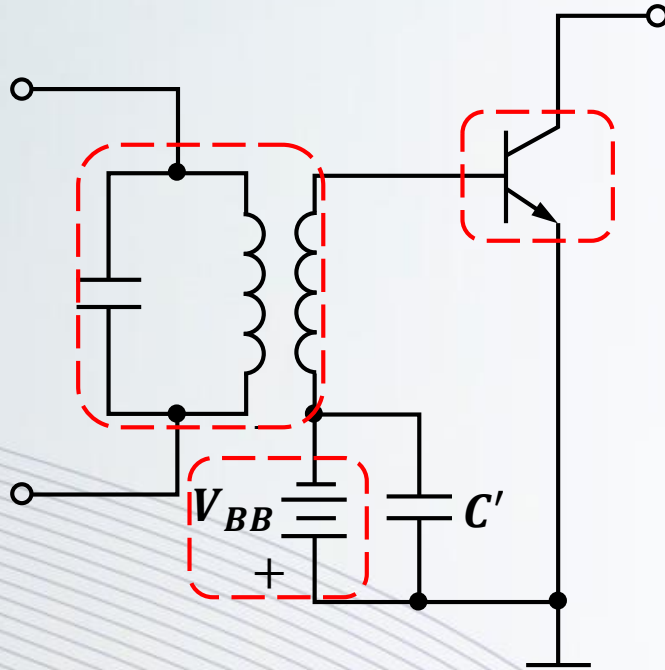
- Fig. (a) : DC Power Supply
- Fig. (b) : $1 \times$ Harmonic Frequency
- Fig. (c) : $\geq 2 \times$ Harmonic Frequency



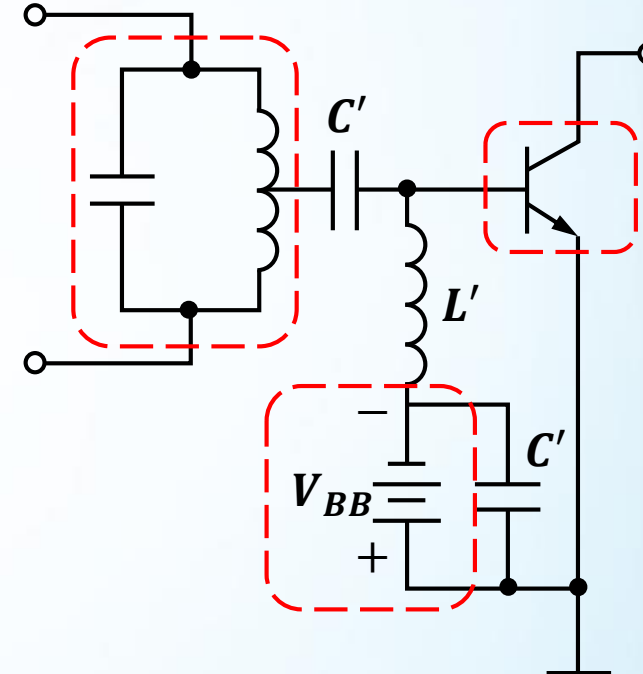
Collector Bias **Equivalent** Circuit for Different Frequency

RF Power Amplifier—Base **Reverse** Bias Circuit

- Series-fed: V_{BB} + Source + Power Amplifier Transistor
- Parallel-fed: V_{BB} // Source // Power Amplifier Transistor

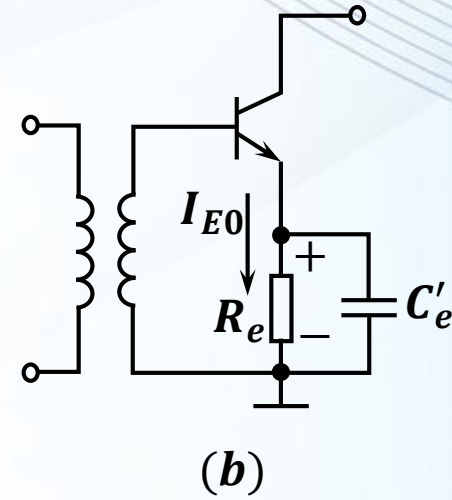
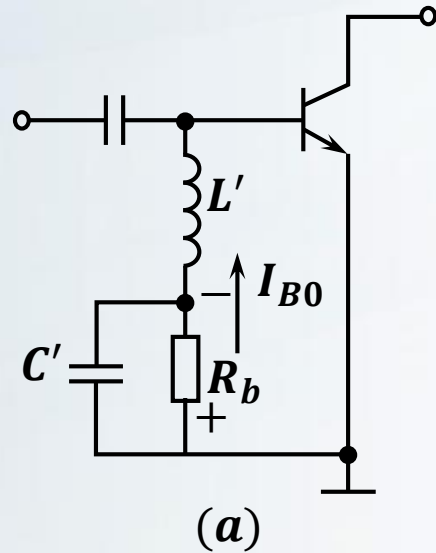


Series-fed

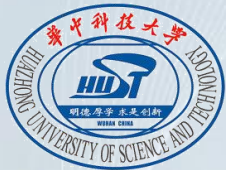


Parallel-fed

RF Power Amplifier—Base Reverse Bias Circuit (Self-Bias)



- Fig(a): Base current I_{B0} on R_b to generate reverse bias voltage V_{BB}
- Fig(b): Emitter current I_{E0} on R_e to generate reverse bias voltage V_{BB}
 - Self Reverse Bias + Negative FeedBack, (For Stability)



C Frequency Multiplier

Class C Frequency Multiplier

➤ Objectives

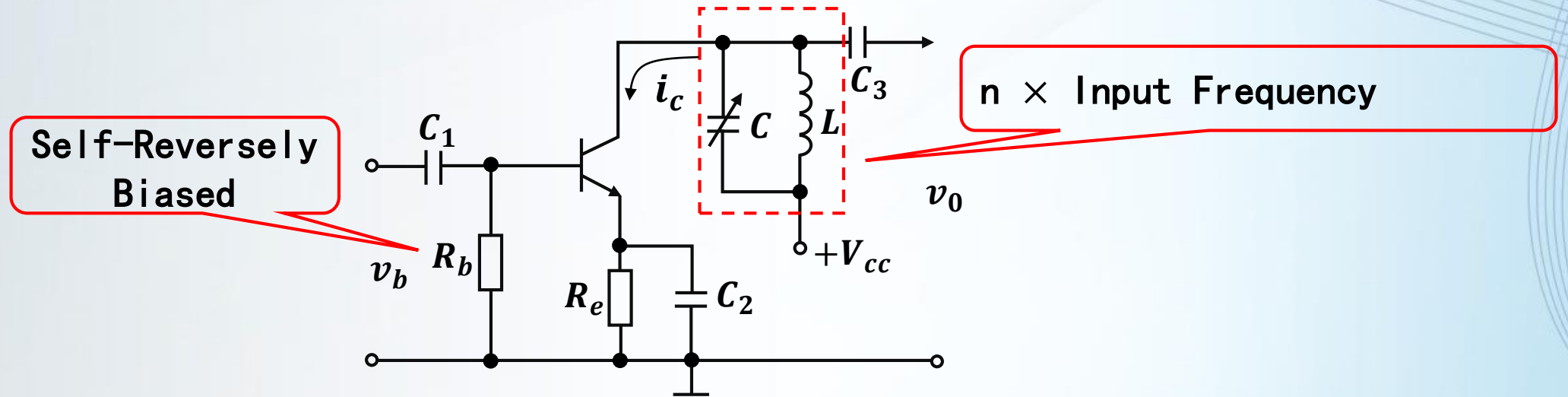
- Decrease frequency of master oscillators, increase stability of frequency
- Obtain higher frequency as quartz crystal oscillators have upper limits
- Decrease intercoupling between input & output frequency, increase stability of frequency
- Increase frequency deviation (FM, PM)
- Increase bandwidth

➤ Method

- Class C Frequency Multiplier

Class C Frequency Multiplier—Principle

- Similar as RF Power Amplifier: Class C, Reversely Biased
- Different: Parallel Resonant on n Times of Input Frequency

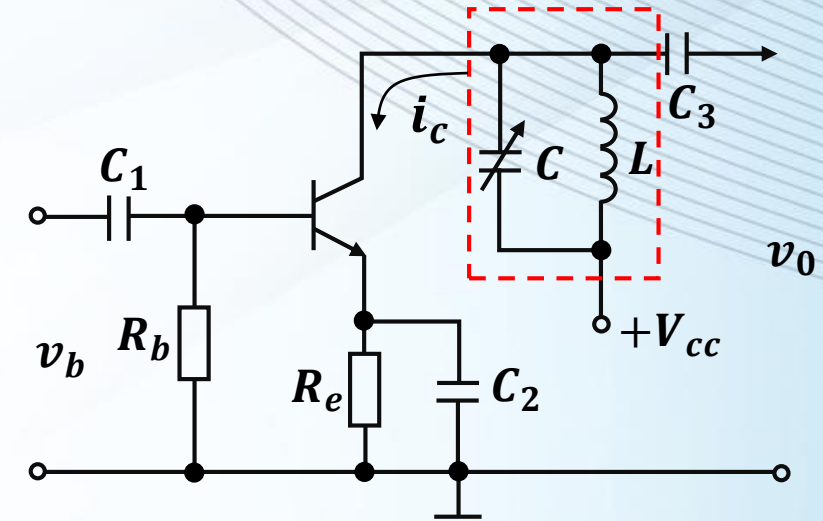
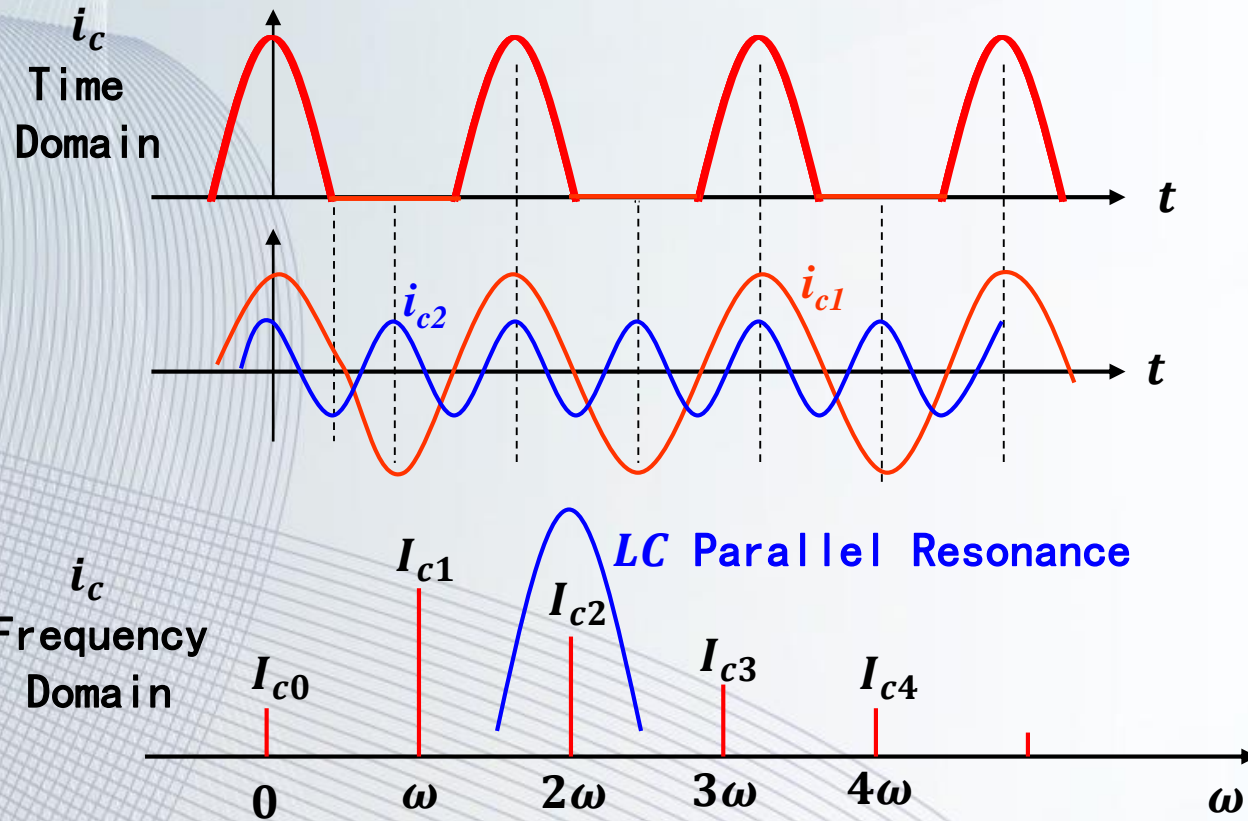


Class C Frequency Multiplier

$$i_c = I_{c0} + I_{cm1} \cos \omega t + I_{cm2} \cos 2\omega t + \cdots + I_{cmn} \cos n\omega t + \cdots$$

Class C Frequency Multiplier—Time & Frequency Domain

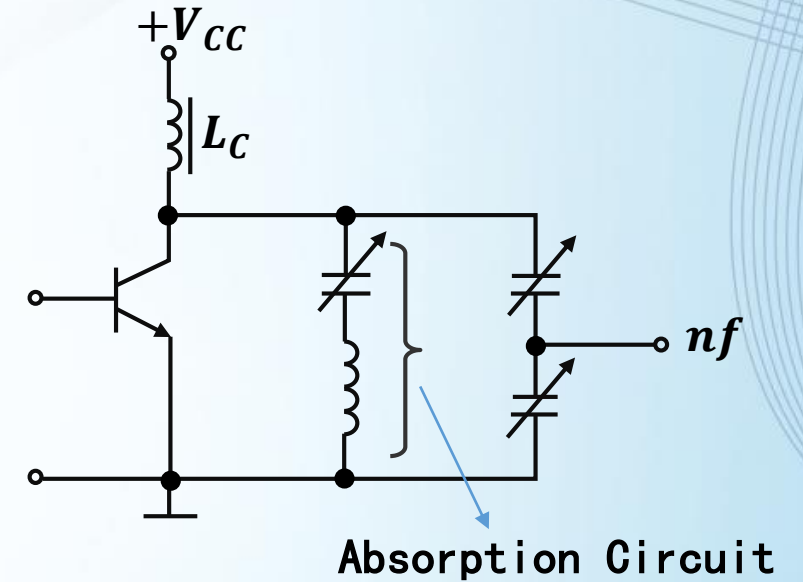
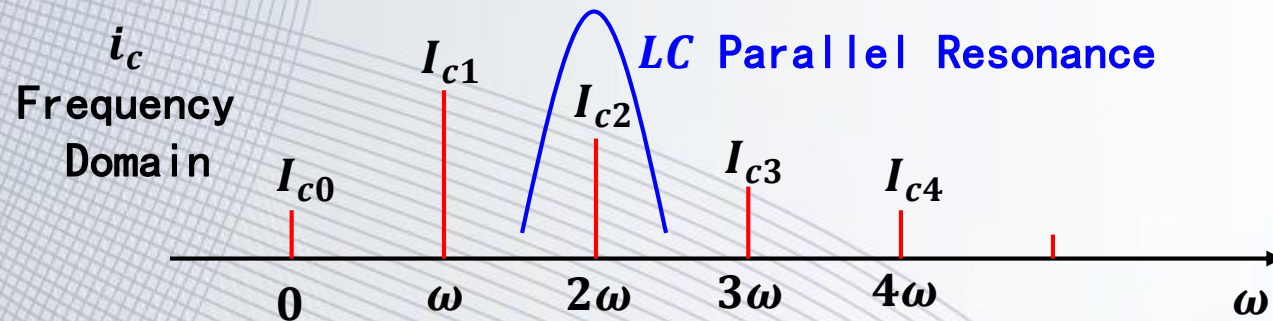
➤ $2 \times$ Input Frequency



Class C Frequency Multiplier

Class C Frequency Multiplier—Filtering

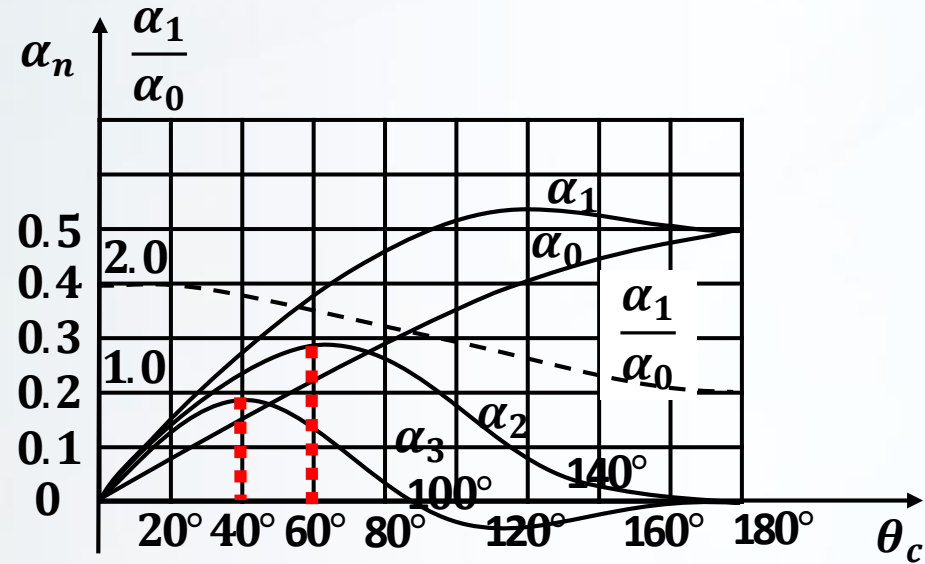
- For C Power Amplifier, easy to remove high frequency
- For C Frequency Multiplier, not easy to remove low frequency
- Increase Filtering Performance:
 - (1) Increase Q
 - (2) Adopt **Absorption Circuit**
 - (3) Increase Selectivity of BPF



Class C Frequency Multiplier— θ_c

➤ How to determine θ_c

Depend on Multiplier n



➤ $n=2$ θ_c round 60°

➤ $n=3$ θ_c round 40°